

P-Channel Enhancement Mode MOSFET

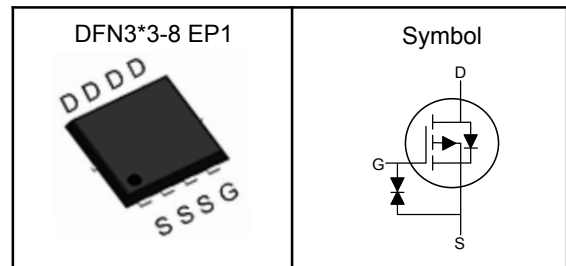
Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available
- ESD Protected 2KV Embedded

Applications

- Power Management in Desktop Computer
- DC/DC Converters

Pin Description



V _{DSS}	-30	V
R _{DS(ON)-Typ}	6.8	mΩ
I _D	-62	A

Absolute Maximum Ratings (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter	P-Channel	Unit	
V _{DSS}	Drain-Source Voltage	-30	V	
V _{GSS}	Gate-Source Voltage	±20	V	
T _J	Maximum Junction Temperature	-55 to 150	°C	
T _{STG}	Storage Temperature Range	-55 to 150	°C	
I _{DM} ^①	Pulse Drain Current Tested	-248	A	
I _D	Continuous Drain Current	T _A =25°C	-16	A
I _D	Continuous Drain Current	T _C =25°C	-62	A
P _D	Maximum Power Dissipation	T _A =25°C	3	W
P _D	Maximum Power Dissipation	T _C =25°C	46	W
E _{AS}	Avalanche Energy, Single pulse	144	mJ	

Thermal Characteristics

Symbol	Parameter	Rating	Unit
R _{θJA}	Thermal Resistance-Junction to Ambient	80	°C/W
R _{θJC}	Thermal Resistance-Junction to Case	2.7	°C/W

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C.

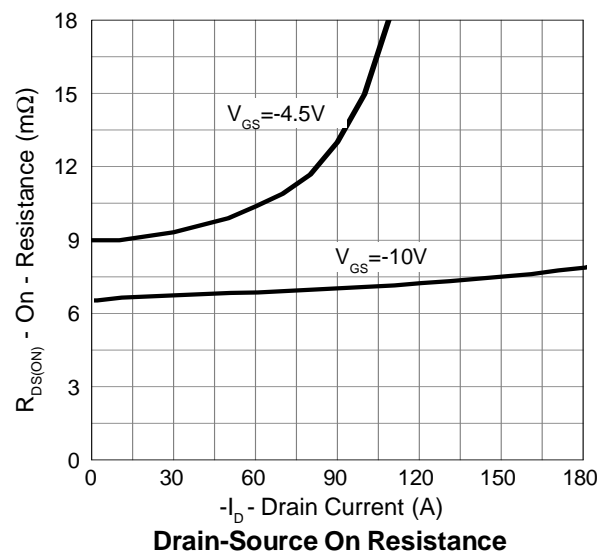
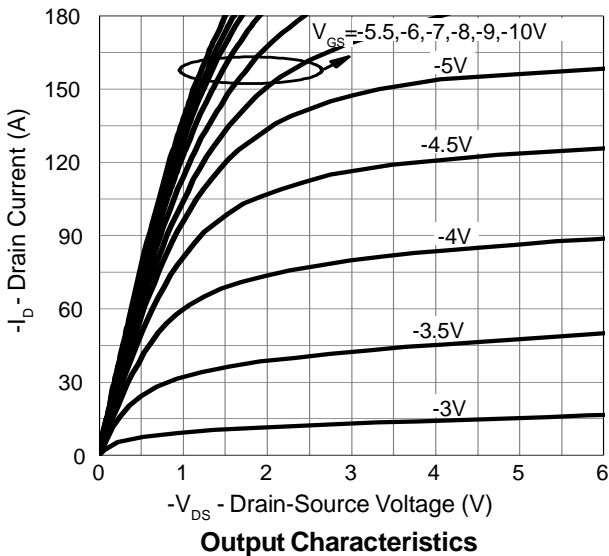
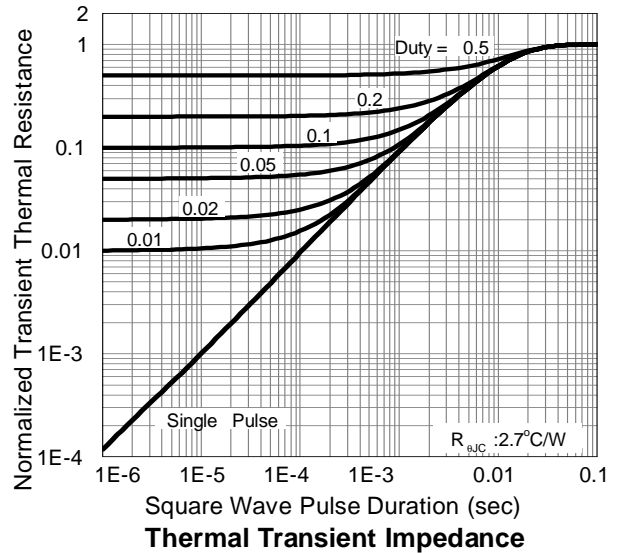
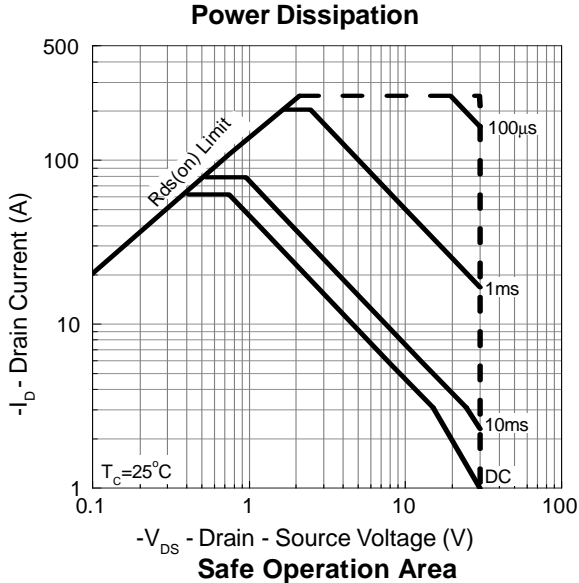
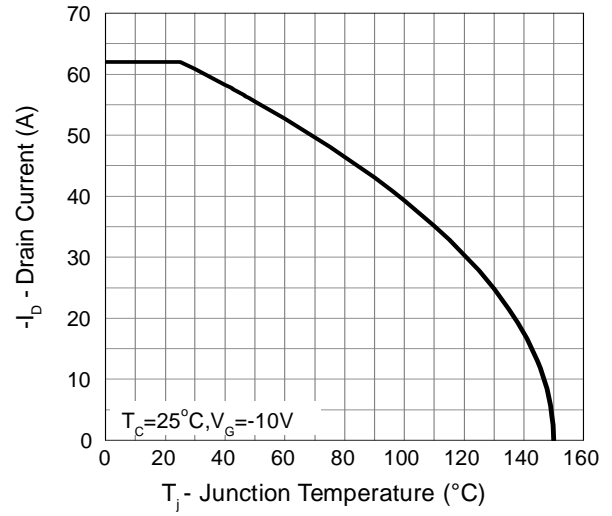
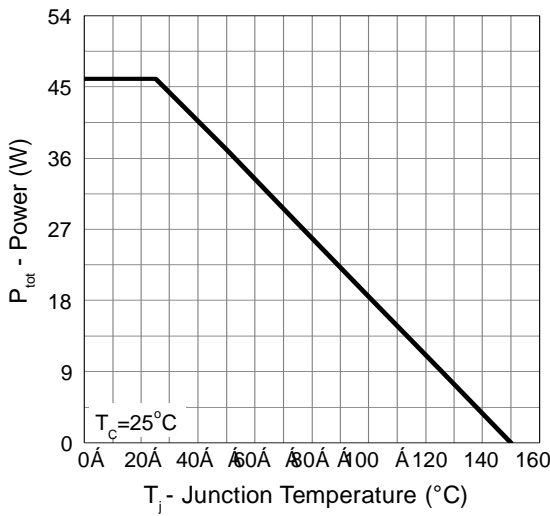
Note ③ : Surface Mounted on 1in² FR-4 board with 1oz.

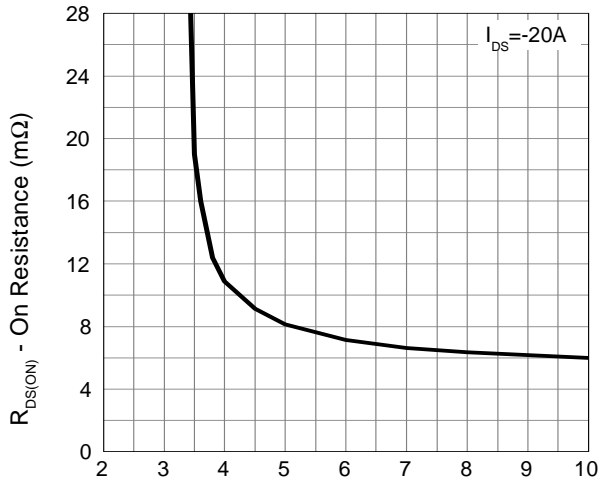
**P-Channel Enhancement Mode MOSFET****Electrical Characteristics** ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24V, V_{GS}=0V$	---	---	-1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.3	---	-2.3	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 10	μA
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS}=-10V, I_D=-20A$	---	6.8	7.8	$m\Omega$
		$V_{GS}=-4.5V, I_D=-10A$	---	9	13	$m\Omega$
Dynamic Characteristics^⑤						
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=-15V, \text{Freq.}=1\text{MHz}$	---	2893	---	pF
C_{oss}	Output Capacitance		---	629	---	
C_{rss}	Reverse Transfer Capacitance		---	513	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=6\Omega, R_L=15\Omega, I_D=-1A$	---	15	---	nS
T_r	Turn-on Rise Time		---	13	---	
$T_{d(off)}$	Turn-off Delay Time		---	58	---	
T_f	Turn-off Fall Time		---	23	---	
Q_g	Total Gate Charge	$V_{DS}=-15V, V_{GS}=-10V, I_D=-20A$	---	62	---	nC
Q_{gs}	Gate-Source Charge		---	7.2	---	
Q_{gd}	Gate-Drain Charge		---	19	---	
Source-Drain Characteristics						
$V_{SD}^{④}$	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	-0.7	-1.0	V
t_{rr}	Reverse Recovery Time	$I_F=-20A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	32	---	nS
Q_{rr}	Reverse Recovery Charge		---	17	---	nC

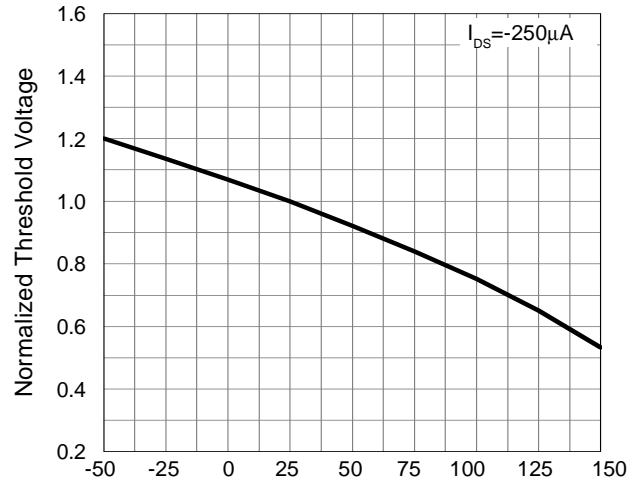
Note ④: Pulse test (pulse width 300 μs , duty cycle 2%).

Note ⑤: Guaranteed by design, not subject to production testing.

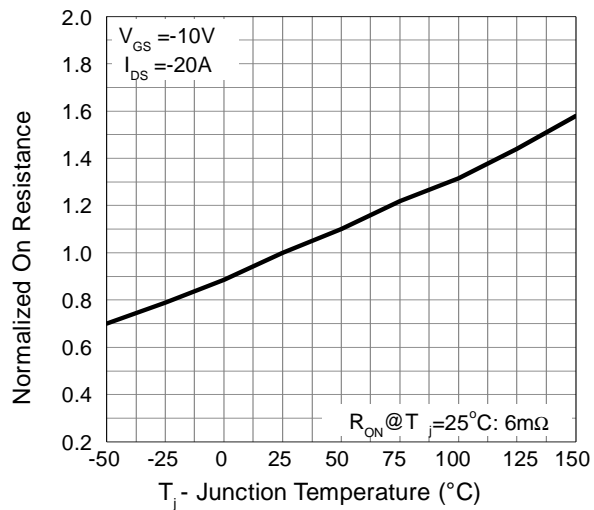
P-Channel Enhancement Mode MOSFET
Typical Characteristics


P-Channel Enhancement Mode MOSFET


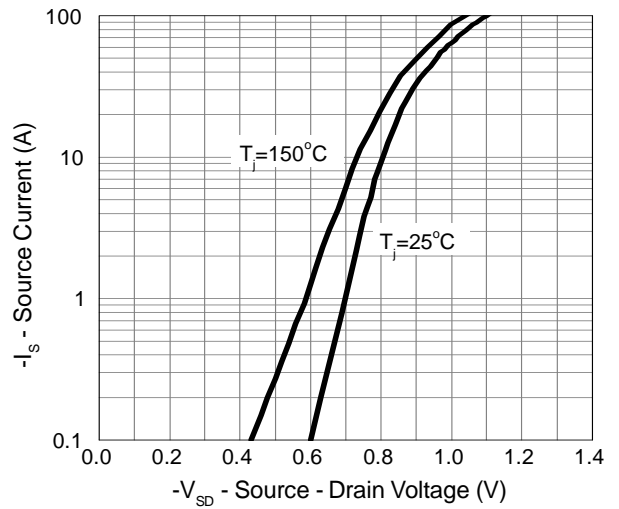
$-V_{GS}$ - Gate - Source Voltage (V)
Gate-Source On Resistance



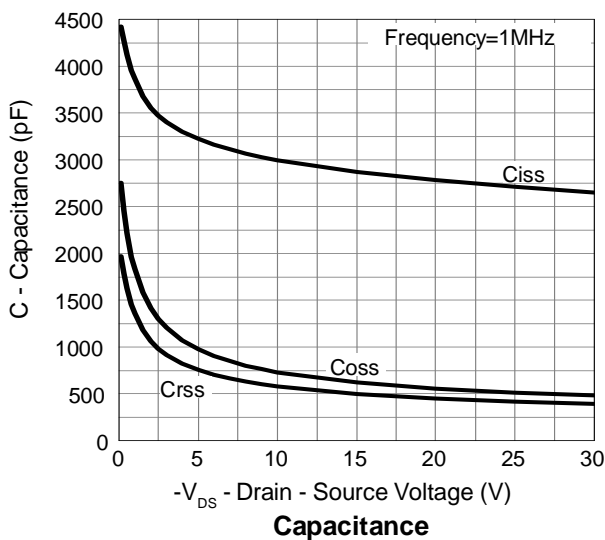
T_j - Junction Temperature ($^{\circ}C$)
Gate Threshold Voltage



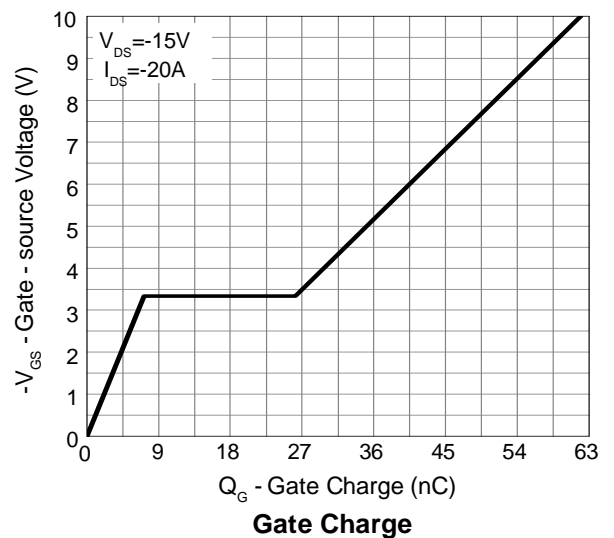
T_j - Junction Temperature ($^{\circ}C$)
Drain-Source On Resistance



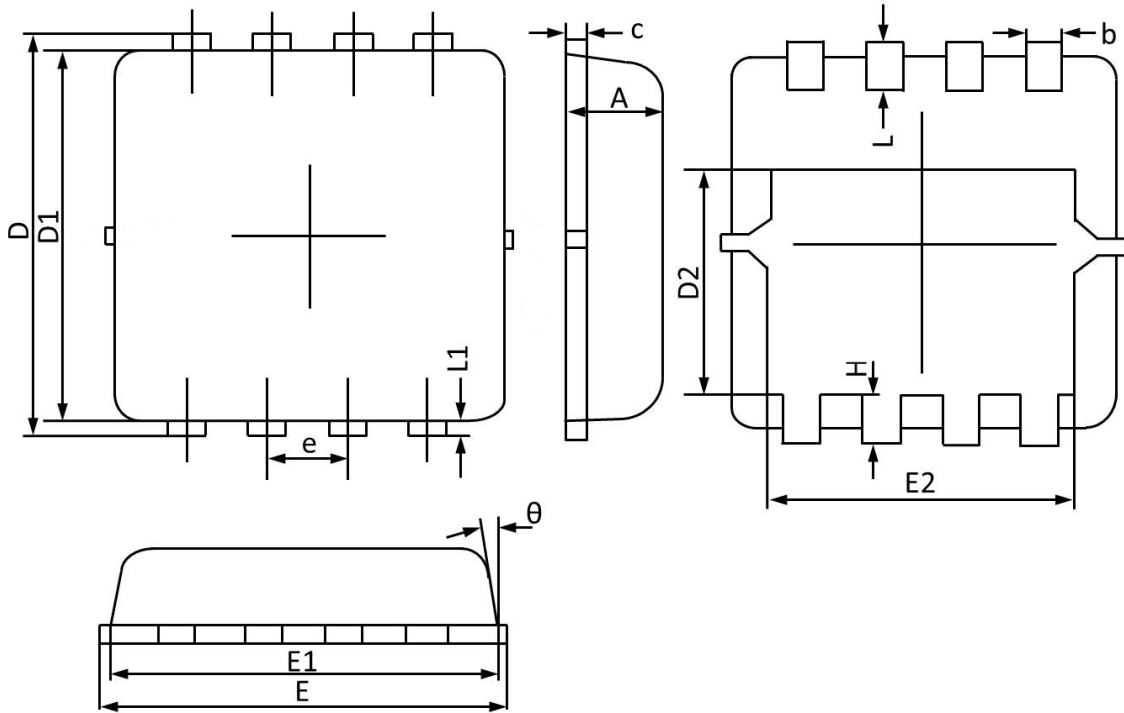
Source-Drain Diode Forward



Capacitance



Gate Charge

P-Channel Enhancement Mode MOSFET
DFN3*3-8 EP1 Package Outline Dimensions


Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.70	0.75	0.85	E1	2.90	3.10	3.25
b	0.24	0.30	0.35	E2	2.35	2.50	2.60
c	0.10	0.17	0.25	e	0.65 BSC		
D	3.10	3.30	3.45	H	0.30	0.40	0.50
D1	2.90	3.05	3.20	L	0.30	0.40	0.50
D2	1.45	1.70	1.95	L1	--	0.13	--
E	3.05	3.25	3.40	theta	0°		14°